

# swissbit®

## Product Fact Sheet

### Industrial / Automotive e•MMC Memory

#### EM-36 Series

JEDEC e•MMC 5.1 compliant,  
BGA 153 ball, Enhanced Mode (pSLC)

Industrial / Automotive  
Temperature Grade

Date: March 25, 2022  
Revision: 1.03



## Product Summary

- **Capacities:** 5 GBytes, 10 GBytes, 20 GBytes, 40 GBytes, 80 GBytes
- **Operating Temperature Range<sup>1</sup>:** Industrial Operating Temperature -40 to 85°C / Automotive Operating Temperature -40 to 105°C (not available for 5 GBytes)
- **Endurance in TeraBytes Written (TBW) @ Max Capacity<sup>2</sup>:** up to 2652

## Product Features

- Fully compliant with JEDEC e-MMC 5.1 Standard (JESD84-B51)
- 153-ball BGA, 0.5mm pitch
- 11.5 x 13mm, RoHS compliant
- 3D TLC NAND base technology in Enhanced Mode (pSLC)
- Industrial Operating Temperature -40 to 85°C / Automotive Operating Temperature -40 to 105°C (not available for 5 GBytes)
- Single enhanced mode partition
- High performance e-MMC 5.1 specification
  - Eleven-wire bus (clock, Data Strobe, 1 bit command, 8 bit data bus) and a hardware reset
  - Three different data bus width modes: 1-bit (default), 4-bit, and 8-bit
  - Clock frequencies 0-200MHz, High Speed Mode HS400
  - Command Queue Feature according to e-MMC Spec 5.1
  - Up to 300MB/s sequential read and up to 230MB/s sequential write
- Power Supply: (Low-power CMOS technology)
  - VCCQ 1.7V...1.95V or 2.7V...3.6V e-MMC supply
  - VCC 2.7V...3.6V NAND Flash supply
- Optimized FW algorithms
  - Power-fail data loss protection
  - Wear Leveling technology  
Equal wear leveling of static and dynamic data. The wear leveling assures that dynamic data as well as static data is balanced evenly across the memory. With that the maximum write endurance of the device is ensured
  - Read Disturb Management  
The read commands per region are monitored and the content is conditionally refreshed when critical levels have occurred
  - Auto Read Refresh  
The interruptible background process maintains the user data for Read Disturb effects or Retention degradation due to high temperature effects
  - Diagnostic features with Device Health Report according to e-MMC Spec 5.1, and detailed Lifetime Monitor data (Swissbit proprietary, accessible through standard e-MMC commands)
  - Field Firmware update<sup>3</sup> according to e-MMC Spec 5.1
  - Discard and Sanitize, Trim
  - Boot Operation Mode and Alternative Boot Operation Mode
  - Replay Protected Memory Block (RPMB)



<sup>1</sup> Adequate airflow is required to ensure the temperature does not exceed 85°C (industrial temperature drive)

<sup>2</sup> According to JEDEC (JESD471), the time to write the full TBW is a minimum of 18 months. Higher average daily data volume reduces the specified TBW. The values listed are estimates and are subject to change without notice.

<sup>3</sup> The support of In-Field FW update capabilities on host systems is recommended.

# Product Fact Sheet

## EM-36 Series



- High reliability
  - Designed with sophisticated firmware architecture for industrial and embedded markets.
  - Enhanced Mode (pSLC) with higher write performance and endurance than 3D TLC configured products (EM-30).
  - Ideal for application like POS/POI, PLC, IoT, gaming, medical and use as general boot medium for embedded applications.
  - The product is optimized for long life cycle that requires superior data retention as well as power fail safety.
  - Controlled BOM & PCN process

## 1 Order Information for EM-36

Density	Part Number	Industrial Temp. Range	Firmware	Flash Technology
5GB	SFEM005GB1ED1T0-I-5E-11P-STD	-40°C to 85°C	FW1: default	3D TLC NAND Flash in pSLC Mode
	SFEM005GB2ED1T0-I-5E-11P-STD			
10GB	SFEM010GB1ED1T0-I-5E-11P-STD			
	SFEM010GB2ED1T0-I-5E-11P-STD			
20GB	SFEM020GB1ED1T0-I-6F-11P-STD			
	SFEM020GB2ED1T0-I-6F-11P-STD			
40GB	SFEM040GB1ED1T0-I-7G-11P-STD			
	SFEM040GB2ED1T0-I-7G-11P-STD			
80GB	SFEM080GB1ED1T0-I-8H-11P-STD			
	SFEM080GB2ED1T0-I-8H-11P-STD			

Density	Part Number	Automotive Temp. Range	Firmware	Flash Technology
10GB	SFEM010GB2ED1T0-A-5E-11P-STD	-40°C to 105°C	FW1: default	3D TLC NAND Flash in pSLC Mode
20GB	SFEM020GB2ED1T0-A-6F-11P-STD			
40GB	SFEM040GB2ED1T0-A-7G-11P-STD			
80GB	SFEM080GB2ED1T0-A-8H-11P-STD			

### 1.1 System Performance

System Performance, HS400	Max. reliable mode	Unit
Burst Data transfer Rate HS400 (max clock 200MHz)	400	MB/s
Sequential Read	up to 300	
Sequential Write	up to 230	

### 1.2 Current Consumption

Current Consumption, HS400, Max. Density	Typ. ICCQ current @ VCCQ 1.8V	Typ. ICC current @ VCC 3.3V	Unit
Write	99	97	mA
Read	138	108	
Sleep	0.07	0.07	

### 1.3 Physical Dimensions

Physical Dimensions	Value	Unit
Length	13±0.1	mm
Width	11.5±0.1	
Thickness	1.2 max.	